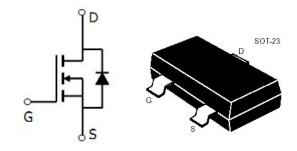
GMS2302AL

SOT-23 場效應晶體管(SOT-23 Field Effect Transistors)



# N-Channel Enhancement-Mode MOS FETs

N 沟道增强型 MOS 场效应管

## ■MAXIMUM RATINGS 最大額定値

Characteristic 特性參數	Symbol 符號	Max 最大値	Unit 單位
Drain-Source Voltage 漏極 - 源極電壓	$\mathrm{BV}_{\mathrm{DSS}}$	20	V
Gate- Source Voltage 栅極-源極電壓	$ m V_{GS}$	<u>+</u> 8	V
Drain Current (continuous) 漏極電流 - 連續	$I_D$	2.6	A
Drain Current (pulsed) 漏極電流-脉冲	${ m I}_{ m DM}$	10	A
Total Device Dissipation 總耗散功率 T <sub>A</sub> =25℃環境溫度爲 25℃	$P_{\mathrm{D}}$	900	mW
Junction 結溫	$\mathrm{T}_{\mathtt{J}}$	150	$^{\circ}\! \mathbb{C}$
Storage Temperature 儲存溫度	$T_{ m stg}$	-55to+150	°C

# **■DEVICE MARKING** 打標

GMS2302AL=A2SHB

GMS2302AL

# ■ELECTRICAL CHARACTERISTICS 電特性

(T<sub>A</sub>=25℃ unless otherwise noted 如無特殊說明,溫度爲 25℃)

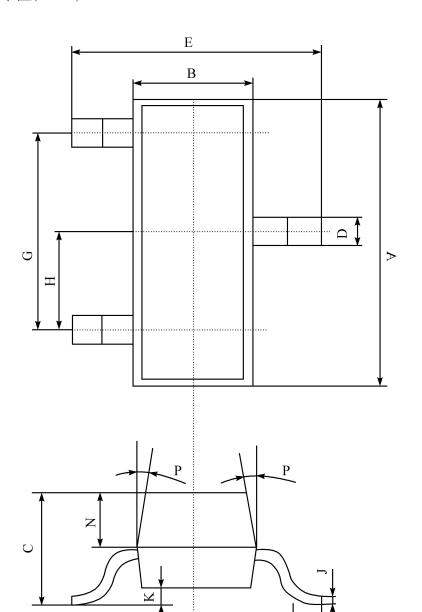
Characteristic 特性參數	Symbol 符號	Min 最小値	Typ 典型値	Max 最大値	Unit 單位
Drain-Source Breakdown Voltage 漏極-源極擊穿電壓(I <sub>D</sub> = 250uA,V <sub>GS</sub> =0V)	BVDSS	20	_	_	V
Gate Threshold Voltage 栅極開启電壓(I <sub>D</sub> = 250uA,V <sub>GS</sub> = V <sub>DS</sub> )	V <sub>GS(th)</sub>	0.4	_	1.5	V
Drain-Source On Voltage 漏極-源極導通電壓(I <sub>D</sub> = 50mA,V <sub>GS</sub> = 5V) (I <sub>D</sub> = 500mA,V <sub>GS</sub> = 10V)	V <sub>DS(ON)</sub>	_	_	0.375 3.75	V
Diode Forward Voltage Drop 内附二極管正向壓降(I <sub>s</sub> = 0.75A,V <sub>GS</sub> =0V)	V <sub>SD</sub>	_	_	1.2	V
Zero Gate Voltage Drain Current 零栅壓漏極電流(V <sub>GS</sub> =0V, V <sub>DS</sub> = 16V) (V <sub>GS</sub> =0V, V <sub>DS</sub> = 16V, T <sub>A</sub> =55℃)	I <sub>DSS</sub>		_	1 10	uA
Gate Body Leakage 栅極漏電流(V <sub>GS</sub> = <u>+</u> 8V, V <sub>DS</sub> =0V)	IGSS		_	<u>+</u> 100	nA
Static Drain-Source On-State Resistance 静态漏源導通電阻(I <sub>D</sub> =2.6A,V <sub>GS</sub> =4.5V) (I <sub>D</sub> =2A,V <sub>GS</sub> =2.5V)	R <sub>DS(ON)</sub>		_	85 120	mΩ
Input Capacitance 輸入電容 (V <sub>GS</sub> =0V, V <sub>DS</sub> = 6V,f=1MHz)	C <sub>ISS</sub>	_	_	880	pF
Common Source Output Capacitance 共源輸出電容(V <sub>GS</sub> =0V, V <sub>DS</sub> = 6V,f=1MHz)	Coss	_	_	270	pF
Turn-ON Time 开启時間 (V <sub>DS</sub> = 6V, I <sub>D</sub> = 1A, R <sub>GEN</sub> =6Ω)	t(on)			20	ns
Turn-OFF Time 关断時間 (V <sub>DS</sub> = 6V, I <sub>D</sub> = 1A, R <sub>GEN</sub> =6Ω)	t <sub>(off)</sub>	_	_	65	ns

Pulse Width≤300 *μ* s; Duty Cycle≤2.0%

GMS2302AL

# ■DIMENSION 外形封裝尺寸

單位(UNIT): mm



M

序號	數值及公差
A	$2.90 \pm 0.10$
В	$1.30 \pm 0.10$
С	$1.00\pm 0.10$
D	$0.40 \pm 0.10$
Е	$2.40\pm0.20$
G	$1.90 \pm 0.10$
Н	$0.95 \pm 0.05$
J	$0.13 \pm 0.05$
K	0.00-0.10
M	≥0.2
N	$0.60\pm 0.10$
P	7 ± 2°